

# General Purpose Transistors

## PNP Silicon

### FEATURE

- High current capacity in compact package.  
 $I_C = -1.5A$ .
- Epitaxial planar type.
- PNP complement: LH8550
- Pb-Free Package is available.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

### DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
(S-)LH8550PLT1G	KIO	3000/Tape&Reel
(S-)LH8550PLT3G	KIO	10000/Tape&Reel
(S-)LH8550QLT1G	KIY	3000/Tape&Reel
(S-)LH8550QLT3G	KIY	10000/Tape&Reel

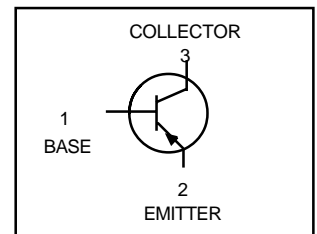
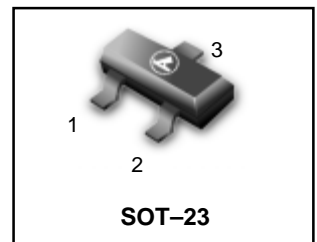
### MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Collector-Base Voltage	$V_{CBO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Collector Current-continuoun	$I_C$	-1500	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Dissipation Power	$P_D$	225	mW
Junction and Storage Temperature	$T_j, T_{stg}$	-55 to +150	°C

LH8550PLT1G  
Series  
S-LH8550PLT1G  
Series



LH8550PLTIG Series,S-LH8550PLTIG Series

ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

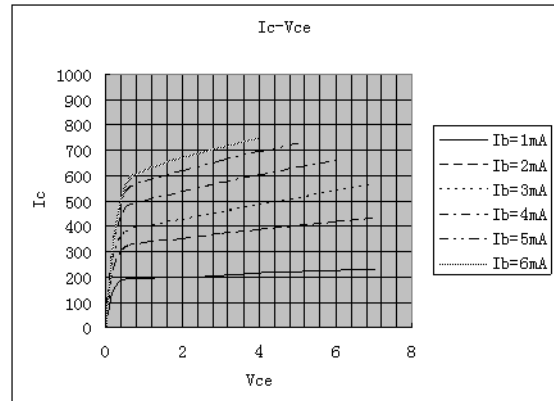
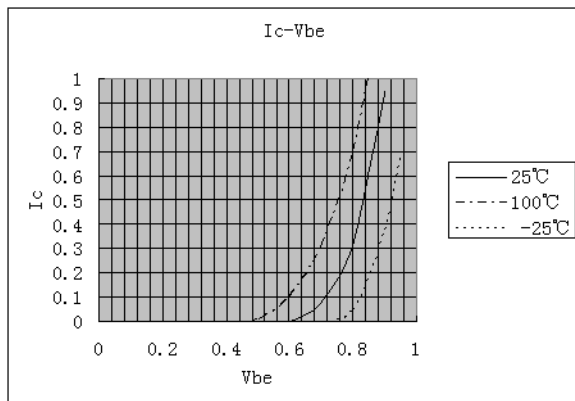
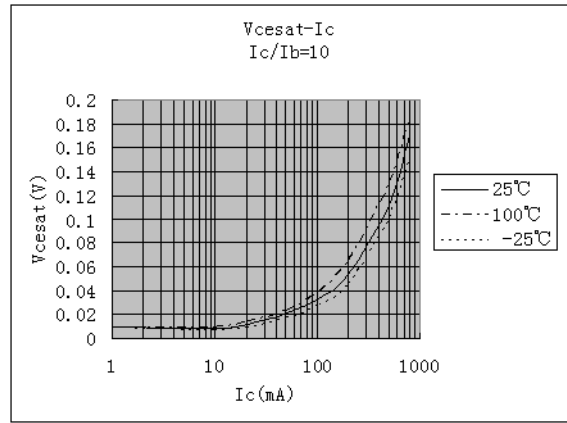
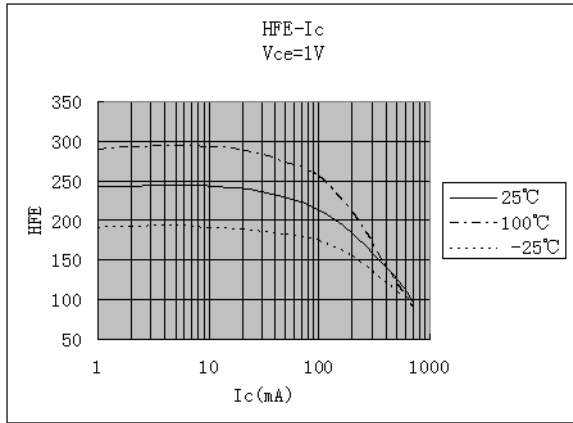
Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage (I <sub>C</sub> =-2.0mA, I <sub>E</sub> =0)	V <sub>(BR)CEO</sub>	-50	-	-	V
Emitter-Base Breakdown Voltage (I <sub>E</sub> =-100μA, I <sub>C</sub> =0)	V <sub>(BR)EBO</sub>	-6	-	-	V
Collector-Base Breakdown Voltage (I <sub>C</sub> =-100μA, I <sub>E</sub> =0)	V <sub>(BR)CBO</sub>	-50	-	-	V
Collector Cutoff Current (V <sub>CE</sub> =-35V, I <sub>E</sub> =0)	I <sub>CBO</sub>	-	-	-100	nA
Emitter Cutoff Current (V <sub>EB</sub> =-6V, I <sub>C</sub> =0)	I <sub>EBO</sub>	-	-	-100	nA
Base-Emitter Voltage (V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA)	V <sub>BE</sub>	-	-0.66	-1	V
DC Current Gain I <sub>C</sub> =-100mA, V <sub>CE</sub> =-1V	h <sub>FE</sub> *	100	-	320	
DC Current Gain I <sub>C</sub> =-800mA, V <sub>CE</sub> =-1V	h <sub>FE</sub>	40	-	-	
Collector-Emitter Saturation Voltage (I <sub>C</sub> =-800mA I <sub>B</sub> =-80mA)	V <sub>CE(S)</sub>	-	-	-0.5	V

NOTE :

*	P	Q
h <sub>FE</sub>	100~200	160~320

LH8550PLTIG Series, S-LH8550PLTIG Series

Electrical Characteristic Curves ( $T_A=25^\circ\text{C}$ )

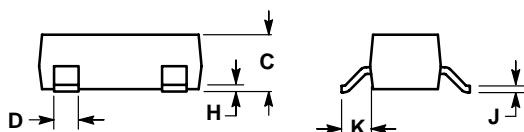
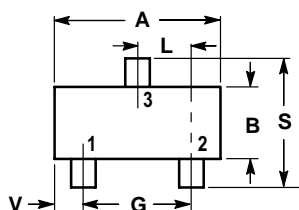


LH8550PLTIG Series, S-LH8550PLTIG Series

SOT-23

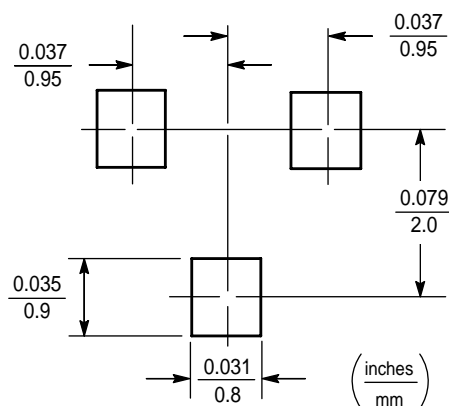
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

PIN 1. BASE  
 2. EMITTER  
 3. COLLECTOR



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